SPICE Model Parameters

Please copy this code from the SPICE model into LTSPICE (version 4) software for simulation of the GB01SHT06-CAU.

```
*      MODEL OF GeneSiC Semiconductor Inc.
*
*      $Revision:   1.0              $
*      $Date:   05-SEP-2013          $
*
*      GeneSiC Semiconductor Inc.
*      43670 Trade Center Place Ste. 155
*      Dulles, VA 20166
*
*      COPYRIGHT (C) 2013 GeneSiC Semiconductor Inc.
*      ALL RIGHTS RESERVED
*
* These models are provided "AS IS, WHERE IS, AND WITH NO WARRANTY
* OF ANY KIND EITHER EXPRESSED OR IMPLIED, INCLUDING BUT NOT LIMITED
* TO ANY IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A
* PARTICULAR PURPOSE."
* Models accurate up to 2 times rated drain current.
*
* Start of GB01SHT06-CAU SPICE Model
*
.SUBCKT GB01SHT06 ANODE KATHODE
D1 ANODE KATHODE GB01SHT06_25C; Call the Schottky Diode Model
D2 ANODE KATHODE GB01SHT06_PIN; Call the PiN Diode Model
.MODEL GB01SHT06_25C D
+ IS       3.57E-18        RS        0.49751
+ TRS1     0.0057          TRS2      2.40E-05
+ N        1               IKF       322
+ EG       1.2             XTI       3
+ CJO      9.12E-11        VJ        0.371817384
+ M        1.527759838     FC        0.5
+ TT       1.00E-10        BV        650
+ IBV      1.00E-03        VPK       650
+ IAVE     1               TYPE      SiC_Schottky
+ MFG      GeneSiC_Semiconductor
.MODEL GB01SHT06_PIN D
+ IS       5.73E-11        RS        0.72994
+ N        5               IKF       800
+ EG       3.23            XTI       -14
+ FC       0.5             TT        0
+ BV       650             IBV       1.00E-03
+ VPK      650             IAVE      1
+ TYPE     SiC_PiN
.ENDS
*
* End of GB01SHT06-CAU SPICE Model
```